Dual 1-of-4 Decoder/Demultiplexer

The MC74AC139/74ACT139 is a high–speed, dual 1–of–4 decoder/demultiplexer. The device has two independent decoders, each accepting two inputs and providing four mutually–exclusive active–LOW outputs. Each decoder has an active–LOW Enable input which can be used as a data input for a 4–output demultiplexer. Each half of the MC74AC139/74ACT139 can be used as a function generator providing four minterms of two variables.

Features

- Multifunctional Capability
- Two Completely Independent 1-of-4 Decoders
- Active LOW Mutually Exclusive Outputs
- Outputs Source/Sink 24 mA
- 'ACT139 Has TTL Compatible Inputs
- These are Pb–Free Devices

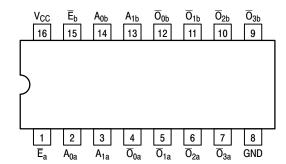


Figure 1. Pinout: 16-Lead Packages Conductors (Top View)

PIN ASSIGNMENT

PIN	FUNCTION
A ₀ , A ₁	Address Inputs
Ē	Enable Inputs
$\overline{O}_0 - \overline{O}_3$	Outputs

TRUTH TABLE

ı	Inputs	}	Outputs					
Ē	A ₀	A ₁	\overline{O}_0 \overline{O}_1 \overline{O}_2 \overline{O}_3					
Н	Χ	Χ	Н	Н	Н	Н		
L	L	L	L	Н	Н	Н		
L	Н	L	Н	L	Н	Н		
L	L	Н	Н	Н	L	Н		
L	Н	Н	Н	Н	Н	L		

H = HIGH Voltage Level L = LOW Voltage Level

X = Immaterial



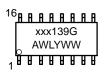
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MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



xxx = AC or ACT

A = Assembly Location WL or L = Wafer Lot

Y = Year
WW or W = Work Week
G or • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

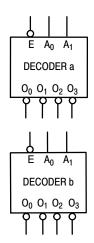
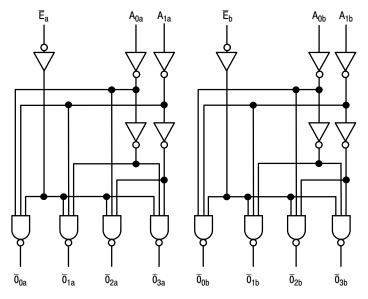


Figure 2. Logic Symbol



NOTE: This diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Figure 3. Logic Diagram

FUNCTIONAL DESCRIPTION

The MC74AC139/74ACT139 is a high–speed dual 1–of–4 decoder/demultiplexer. The device has two independent decoders, each of which accepts two binary weighted inputs (A_0-A_1) and provides four mutually exclusive active–LOW outputs $(\overline{O}_0-\overline{O}_3)$. Each decoder has an active–LOW enable (\overline{E}) . When \overline{E} is HIGH all outputs are forced HIGH. The enable can be used as the data input for a 4–output demultiplexer application. Each half of the MC74AC139/74ACT139 generates all four minterms of two variables. These four minterms are useful in some applications, replacing multiple gate functions as shown in Figure 4, and thereby reducing the number of packages required in a logic network.

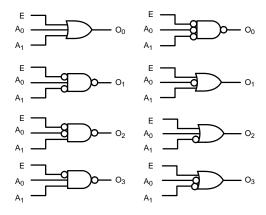


Figure 4. Gate Functions (Each Half)

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		$-0.5 \le V_{I} \le V_{CC} + 0.5$	V
Vo	DC Output Voltage	(Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current		±50	mA
I _O	DC Output Sink/Source Current		±50	mA
I _{CC}	DC Supply Current per Output Pin		±50	mA
I _{GND}	DC Ground Current per Output Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC TSSOP	69.1 103.8	°C/W
P _D	Power Dissipation in Still Air at 65°C (Note 3)	SOIC TSSOP	500 500	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating Oxygen Inc	dex: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}		Model (Note 4) Model (Note 5) Model (Note 6)	> 2000 > 200 > 1000	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND a	at 85°C (Note 7)	± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I_O absolute maximum rating must be observed.
- 2. The package thermal impedance is calculated in accordance with JESD51–7.
- 3. 500 mW at 65°C; derate to 300 mW by 10 mW/ from 65°C to 85°C.
- 4. Tested to EIA/JESD22-A114-A.
- 5. Tested to EIA/JESD22-A115-A.
- 6. Tested to JESD22-C101-A.
- 7. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit		
.,	Owner L. Veller ve	′AC	2.0	5.0	6.0	.,,		
V _{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V		
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Ref. to GND)	0	-	V _{CC}	V			
		V _{CC} @ 3.0 V	-	150	_			
t_r , t_f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	_	ns/V		
	76 Bevious except commit inputs	V _{CC} @ 5.5 V	-	25	_			
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	-	10	_	ns/V		
t _r , t _f	'ACT Devices except Schmitt Inputs	V _{CC} @ 5.5 V	-	8.0	_			
TJ	Junction Temperature (PDIP)	-	-	140	°C			
T _A	Operating Ambient Temperature Range	-40	25	85	°C			
I _{OH}	Output Current – High	-	-	-24	mA			
I _{OL}	Output Current – Low		_	_	24	mA		

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V_{IN} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.
 V_{IN} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74.	AC	74AC		
		V _{CC}	T _A = -	+25°C	T _A = -40°C to +85°C		
Symbol	Parameter	(V)	Тур	Gua	ranteed Limits	Unit	Conditions
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	$V_{OUT} = 0.1 \text{ V}$ or $V_{CC} - 0.1 \text{ V}$
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	Ι _{ΟΟΤ} = -50 μΑ
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ -12 mA I_{OH} -24 mA -24 mA
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	Ι _{ΟΟΤ} = 50 μΑ
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	* V _{IN} = V _{IL} or V _{IH} 12 mA I _{OL} 24 mA 24 mA
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	- 75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	$V_{IN} = V_{CC}$ or GND

^{*}All outputs loaded; thresholds on input associated with output under test.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V_{CC} .

AC CHARACTERISTICS

			74AC T _A = +25°C C _L = 50 pF			$74AC$ $T_A = -40^{\circ}C \text{ to } +85^{\circ}C$ $C_L = 50 \text{ pF}$			Fig.
		V _{CC} *							
Symbol	Parameter	(V)	Min	Тур	Max	Min	Max	Unit	No.
t _{PLH}	Propagation Delay A _n to \overline{O}_n	3.3 5.0	4.0 3.0	8.0 6.5	11.5 8.5	3.5 2.5	13 9.5	ns	3–6
t _{PHL}	Propagation Delay A _n to \overline{O}_n	3.3 5.0	3.0 2.5	7.0 5.5	10 7.5	2.5 2.0	11 8.5	ns	3–6
t _{PLH}	Propagation Delay E _n to O _n	3.3 5.0	4.5 3.5	9.5 7.0	12 8.5	3.5 3.0	13 10	ns	3–6
t _{PHL}	Propagation Delay E _n to O _n	3.3 5.0	4.0 2.5	8.0 6.0	10 7.5	3.0 2.5	11 8.5	ns	3–6

[†]Maximum test duration 2.0 ms, one output loaded at a time.

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. *Voltage Range 5.0 V is 5.0 V ± 0.5 V.

DC CHARACTERISTICS

		74ACT 74ACT		74ACT			
		V _{CC}	T _A =	+25°C	T _A = -40°C to +85°C		
Symbol	Parameter	(V)	Тур	Typ Guaranteed Lim		Unit	Conditions
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	٧	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = -50 μA
		4.5 5.5	- -	3.86 4.86	3.76 4.76	V	$^{*}V_{IN} = V_{IL} \text{ or } V_{IH}$ -24 mA I_{OH} -24 mA
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA
		4.5 5.5	_ _	0.36 0.36	0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ $^{24} \text{ mA}$ $^{1}_{OL}$ $^{24} \text{ mA}$
I _{IN}	Maximum Input Leakage Current	5.5	_	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	-	- 75	mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5	_	8.0	80	μΑ	V _{IN} = V _{CC} or GND

^{*}All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS

				74ACT			CT		
		v _{cc} *	T _A = +25°C C _L = 50 pF			$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ $C_L = 50 \text{ pF}$			Fig.
Symbol	Parameter	(V)	Min	Тур	Max	Min	Max	Unit	No.
t _{PLH}	Propagation Delay A_n to \overline{O}_n	5.0	1.5	6.0	8.5	1.5	9.5	ns	3–6
t _{PHL}	Propagation Delay A_n to \overline{O}_n	5.0	1.5	6.0	9.5	1.5	10.5	ns	3–6
t _{PLH}	Propagation Delay \overline{E}_n to \overline{O}_n	5.0	2.5	7.0	10.0	2.0	11.0	ns	3–6
t _{PHL}	Propagation Delay \overline{E}_n to \overline{O}_n	5.0	2.0	7.0	9.5	1.5	10.5	ns	3–6

^{*}Voltage Range 5.0 V is 5.0 V ± 0.5 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	40	pF	V _{CC} = 5.0 V

ORDERING INFORMATION

Device Order Number	Package	Shipping [†]
MC74AC139DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74AC139DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74AC139DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel
MC74ACT139DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74ACT139DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74ACT139DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN MAX		MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
7	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

16. COLLECTOR 16. CATHODE 16. COLLECTOR, #4 16. EMITTER, #1 STYLE 5: STYLE 6: STYLE 7: PIN 1. DRAIN, DYE #1 PIN 1. CATHODE 2. COMMON DRAIN (OUTPUT) 3. DRAIN, #1 2. CATHODE 2. COMMON DRAIN (OUTPUT) 4. DRAIN, #2 3. CATHODE 3. COMMON DRAIN (OUTPUT) 5. DRAIN, #3 5. CATHODE 4. GATE P-CH 7. DRAIN, #3 6. CATHODE 5. COMMON DRAIN (OUTPUT) 8. DRAIN, #4 7. CATHODE 7. COMMON DRAIN (OUTPUT) 8. DRAIN, #4 8. CATHODE 8. SOURCE P-CH 9. GATE, #4 9. ANODE 9. SOURCE P-CH 10. SOURCE, #4 10. ANODE 10. COMMON DRAIN (OUTPUT) 11. GATE, #3 11. ANODE 11. COMMON DRAIN (OUTPUT) 12. SOURCE, #3 12. ANODE 13. GATE N-CH 14. SOURCE, #2 14. ANODE 14. COMMON DRAIN (OUTPUT) 15. GATE, #1 15. ANODE 16. SOURCE N-CH 16. SOURCE, #1 16. ANODE 16. SOURCE N-CH	STYLE 1: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION	STYLE 3: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3 COLLECTOR, #3 COLLECTOR, #4	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, DYE #1 COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2 EMITTER, #2 BASE, #1		FOOTPRINT
STYLE 5:										
	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN COMMON DRAIN COMMON DRAIN COMMON DRAI	n n n n n n	16X 0.58	<u> </u>	16X 1.12

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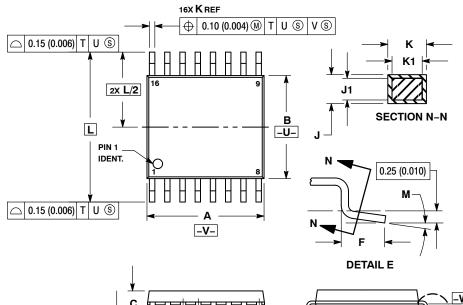
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



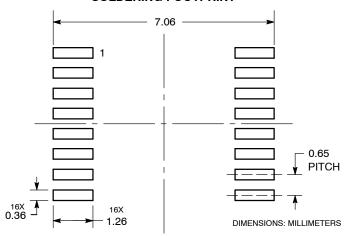
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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